

III - V Microelectronics

by Jean-Pierre Nougier ; EUROFORM (Organization)

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process for selectively introducing controlled amount of n- and p-type impurities in III-V The IHP - Innovations for High Performance Microelectronics III-V microelectronics - CERN Document Server Journal of Microelectronics and Electronic Packaging: January 2012, Vol. effects on the performance and reliability of future digital III-V device are discussed. Recent Soviet microelectronics research on III-V . - ResearchGate